

isc Silicon PNP Power Transistors

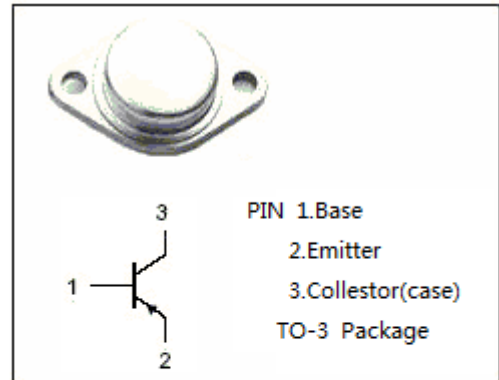
2SB612

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -140V(\text{Min})$
- High Power Dissipation-
: $P_C = 100W(\text{Max}) @ T_C = 25^\circ\text{C}$
- Complement to Type 2SD582

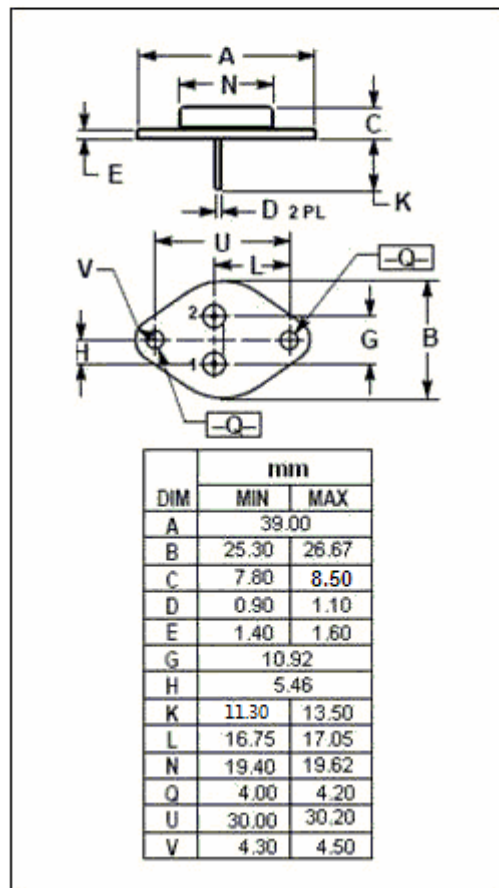
APPLICATIONS

- Recommended for 80~100W audio amplifier output stage.



ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-180	V
V_{CEO}	Collector-Emitter Voltage	-140	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-12	A
I_{CM}	Collector Current-Peak	-15	A
I_B	Collector Current-Continuous	-2	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	100	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



isc Silicon PNP Power Transistors**2SB612****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -30mA; R _{BE} = ∞	-140			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -5mA; I _C = 0	-6			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -7A; I _B = -0.7A			-1.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -1A; V _{CE} = -5V			-1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -160V; I _E = 0			-10	μ A
h _{FE-1}	DC Current Gain	I _C = -1A; V _{CE} = -5V	35		200	
h _{FE-2}	DC Current Gain	I _C = -7A; V _{CE} = -5V	20			

◆ **h_{FE-1} Classifications**

A	B	C
35-70	60-120	100-200